9. (Amended) A micro-hotplate device according to claim 1, wherein the semiconducting material in the island is silicon.

10. (Amended) A micro-hotplate device according to claim 1, wherein the semiconducting material in the island is silicon carbide.

11. (Amended) A micro-hotplate device according to claim 1, wherein the support substrate and the island are made of the same material.

17. (Amended) A method according to claim 12, wherein at least one of said etching steps is an anisotropic potassium hydroxide etching step.

18. (Amended) A method according to claim 12, wherein at least one of said etching steps is an anisotropic tetramethyl ammonium hydroxide etching step.

19. (Amended) A method according to claim 12, wherein at least one of said etching steps is a deep reactive ion etching step.

20. (Amended) A micro-hotplate device according to claim 1, wherein one or several of the chemical sensors utilize the field-effect detection mechanism.

22. (Amended) A micro-hotplate device according to claim 1, wherein one or several of the chemical sensors are operated as gas sensors.

23. (Amended) A micro-hotplate device according to claim 21, wherein one or several field-effect gas sensors are combined with one or several gas sensors that utilize resistance changes as detection mechanism.

26. (Amended) A micro-hotplate device according to claim 1, wherein the support substrate contains an array of several islands.

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